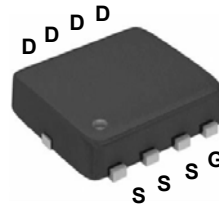
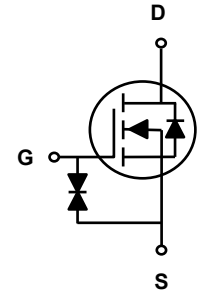


Main Product Characteristics

$V_{(BR)DSS}$	20V
$R_{DS(ON)}$	10m Ω
I_D	30A



PPAK3X3



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFN2310 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current – Continuous (T _C =25°C) (Chip Limitation)	I_D	30	A
Drain Current – Continuous (T _C =100°C) (Chip Limitation)		19	A
Drain Current – Pulsed ₁ (Chip Limitation)	I_{DM}	120	A
Power Dissipation (T _C =25°C)	P_D	26	W
Power Dissipation – Derate above 25°C		0.21	W/°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	---	62	°C/W
Thermal Resistance Junction to Case	$R_{\theta JC}$	---	4.8	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=1\text{mA}$	---	0.02	---	$\text{V}/^{\circ}\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=16V, V_{GS}=0V, T_J=125^{\circ}\text{C}$	---	---	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	---	---	± 100	nA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=5A$	---	8	10	$\text{m}\Omega$
		$V_{GS}=2.5V, I_D=3A$	---	9.5	12	$\text{m}\Omega$
		$V_{GS}=1.8V, I_D=2A$	---	12	17	$\text{m}\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.3	0.6	1	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	2	---	$\text{mV}/^{\circ}\text{C}$
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_S=5A$	---	12	---	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2, 3}	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=5A$	---	16.9	26	nC
Gate-Source Charge ^{2, 3}	Q_{gs}		---	1.1	3	
Gate-Drain Charge ^{2, 3}	Q_{gd}		---	4	7	
Turn-On Delay Time ^{2, 3}	$T_{d(on)}$	$V_{DD}=10V, V_{GS}=4.5V, R_G=25\Omega, I_D=1A$	---	6.8	13	nS
Rise Time ^{2, 3}	T_r		---	20	38	
Turn-Off Delay Time ^{2, 3}	$T_{d(off)}$		---	41.8	79	
Fall Time ^{2, 3}	T_f		---	13.2	25	
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, F=1\text{MHz}$	---	1020	1480	pF
Output Capacitance	C_{oss}		---	160	240	
Reverse Transfer Capacitance	C_{rss}		---	110	160	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	2	4	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_{GS}=V_D=0V, \text{Force Current}$	---	---	30	A
Pulsed Source Current	I_{SM}		---	---	60	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	---	1	V

Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

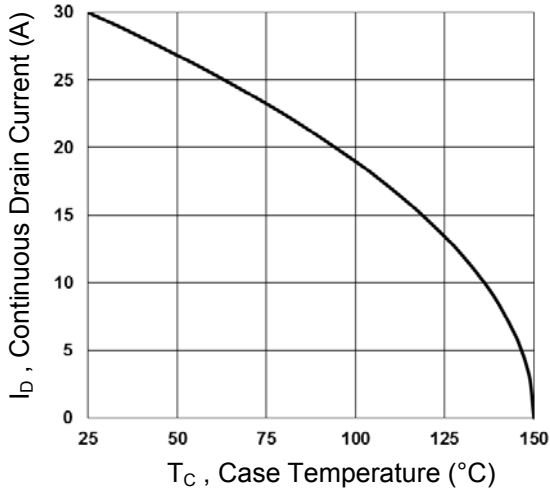


Fig.1 Continuous Drain Current vs. T_c

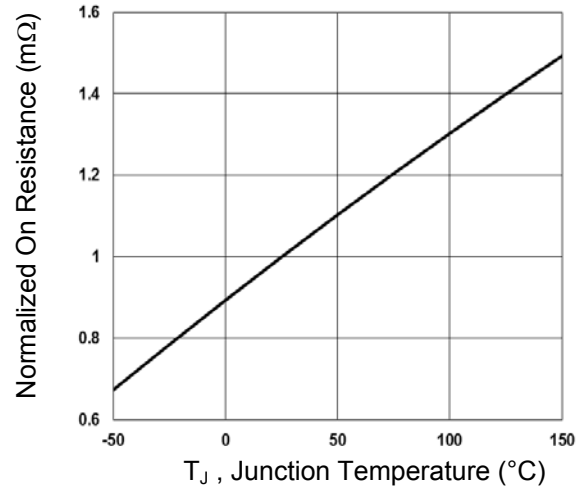


Fig.2 Normalized $R_{DS(ON)}$ vs. T_j

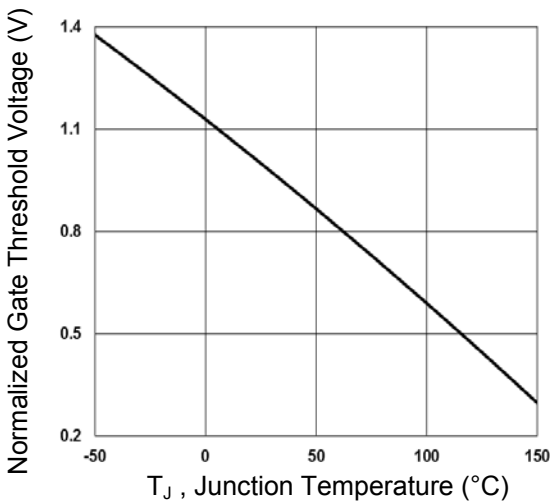


Fig.3 Normalized V_{th} vs. T_j

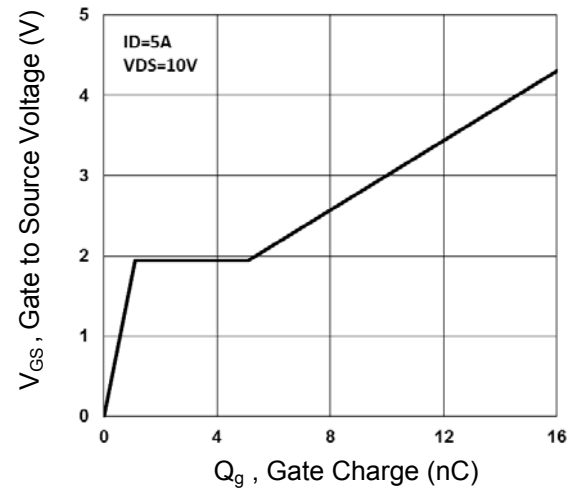


Fig.4 Gate Charge Waveform

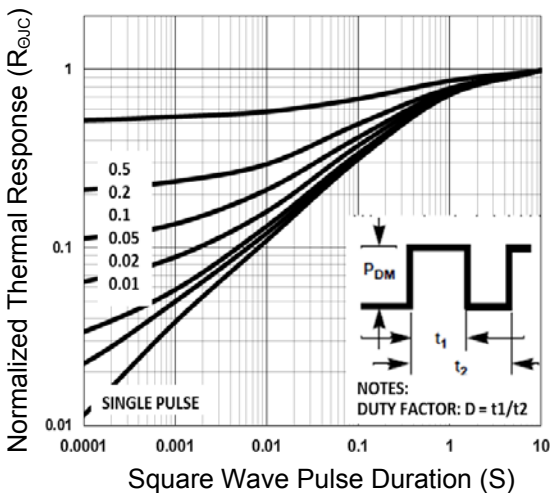


Fig.5 Normalized Transient Response

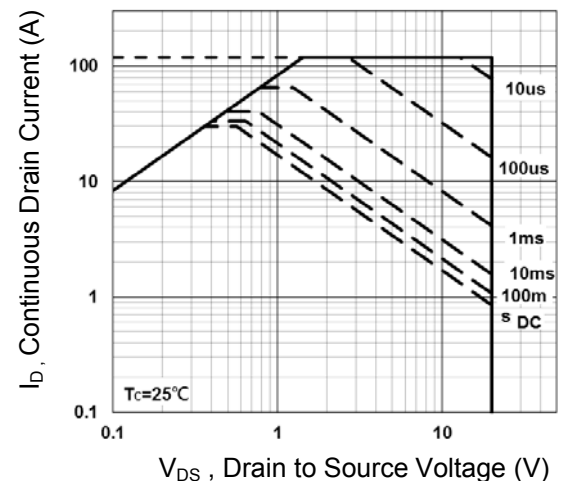


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

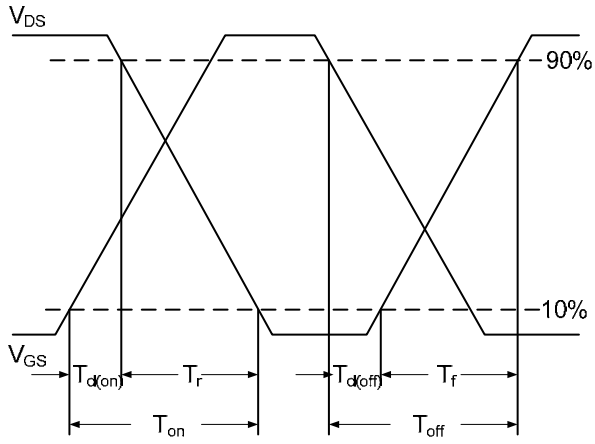


Fig.7 Switching Time Waveform

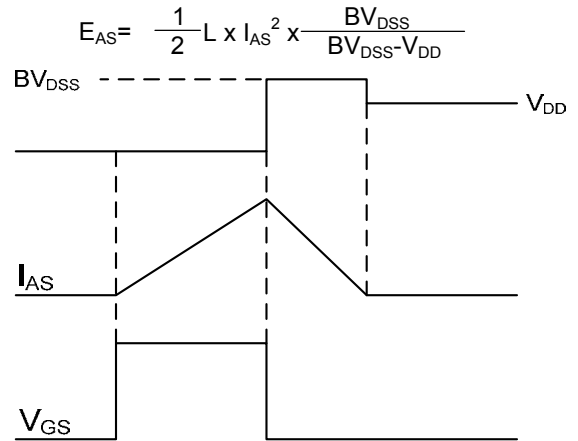
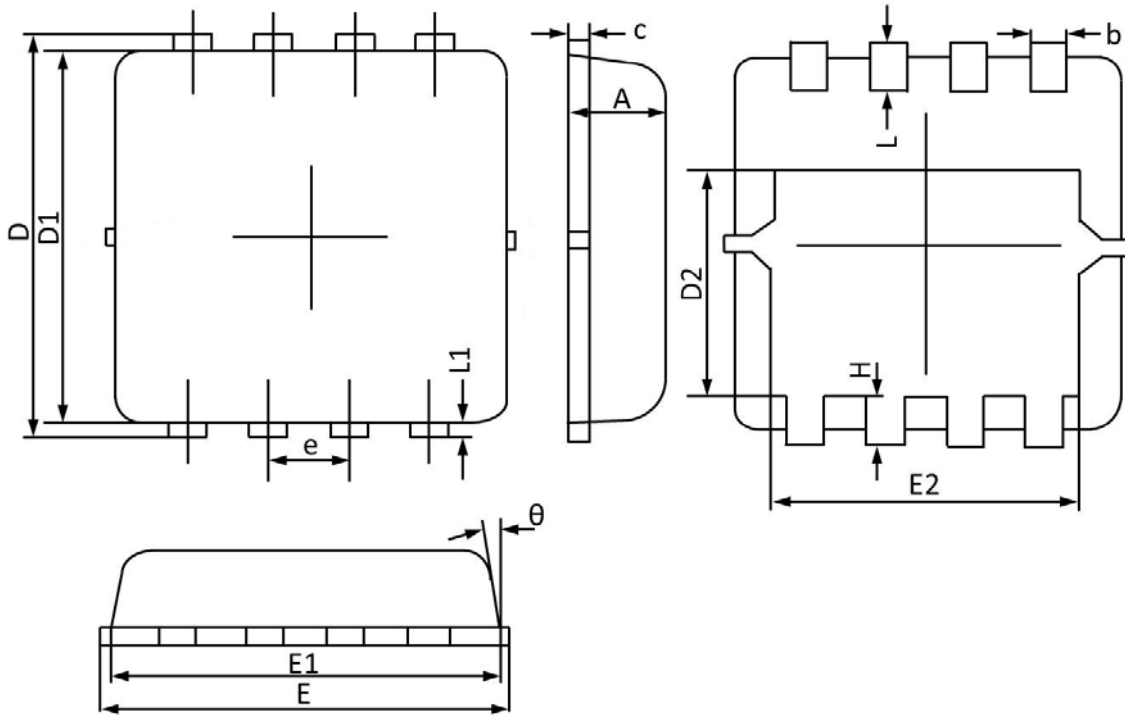


Fig.8 E_{AS} Waveform

Package Outline Dimensions

PPAK3X3



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.240	0.014	0.009
c	0.250	0.100	0.010	0.004
D	3.450	3.050	0.136	0.120
D1	3.200	2.900	0.126	0.114
D2	1.850	1.350	0.073	0.053
E	3.400	3.000	0.134	0.118
E1	3.250	2.900	0.128	0.114
E2	2.600	2.350	0.102	0.093
e	0.65BSC		0.026BSC	
H	0.500	0.300	0.020	0.012
L	0.500	0.300	0.020	0.012
L1	0.200	0.070	0.008	0.003
θ	12°	0°	12°	0°